

Dual MOS, P-channel

TYPE	RATINGS		CHARACTERISTICS					
	BVGSSF	PTOT W	IGSSF	VGS V	VGS(TH)	IDSS nA	rDS(ON) Ω	VGS differential
3N207	-25	0.6	-4 pA	-25	-3 min. -6 max.	-10	400	max. 200 mV
3N208	-30	0.6	-1 nA*	-15	-3 min. -6 max.	-10	400	—

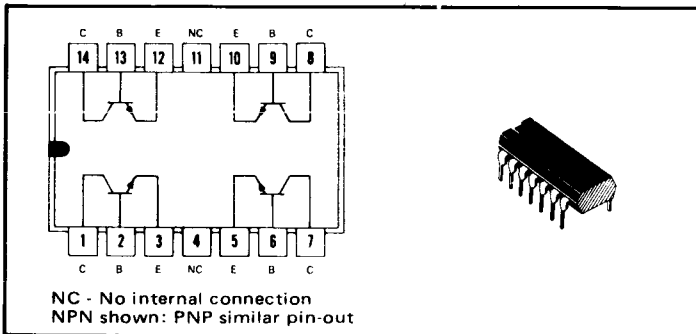
*3N208 incorporates gate protection diodes.

Dual J-FET

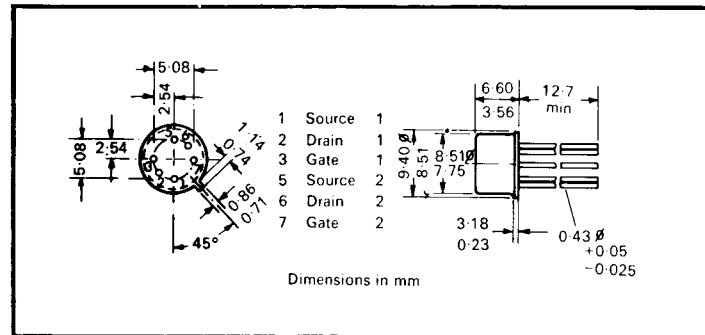
Type No	Pol	BVGSS min V	IGSS max nA	Vp max V	Yfs min μmho	Yfs max μmho	Ciss max pF	Yfs %	Matching VGS mV (1-2)	ΔV_{GS} C (1,2)
TIS25*	N	50	0.25	6	1500	25	8	5	5	70
TIS26*	N	50	0.25	6	1500	25	8	10	10	140
TIS27*	N	50	0.25	6	1500	25	8	20	15	240
2N5045+	N	50	0.25	4.6	1500	25	8	5	5	80
2N5046+	N	50	0.25	4.5	1500	25	8	10	10	160
2N5047+	N	50	0.25	4.5	1500	25	8	20	15	240
2N5545+	N	50	0.1	4.5	1500	25	6	3	5	10
2N5546+	N	50	0.1	4.6	1500	25	6	5	10	20
2N5547+	N	50	0.1	4.5	1500	25	6	10	15	40

*6-PIN-TO5

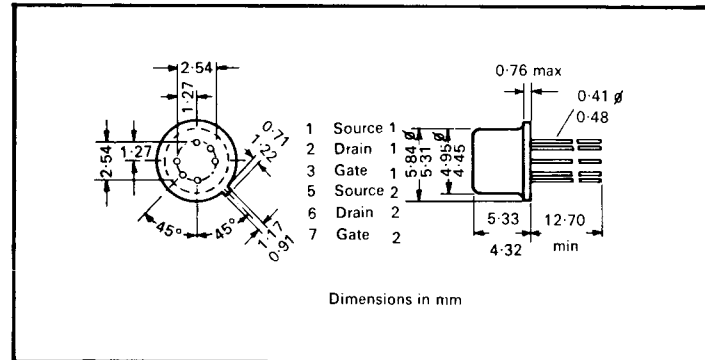
+6-PIN-TO18



Dual-in-line (Plastic)



6 lead TO-5



6 lead TO-18

Monolithic Dual FETS

Type No	Case	Pol	BVGSS min V	IGS max pA	Yfs min mS	CISS max pF	en-100kHz max nV Hz ^{-1/2}	VGS max mV
*BFQ20	TO-71	N	40	30	0.85	7.0	6.0	25
*BFQ21	TO-71	N	40	30	0.85	7.0	6.0	50
*BFQ25	TO-71	N	25	250	9.0	18.0	1.4	25
*BFQ26	TO-71	N	25	250	9.0	18.0	1.4	50